

### 30V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

# **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C		
30V	6mΩ @ V <sub>GS</sub> = 10V	60A		
307	9mΩ @ V <sub>GS</sub> = 4.5V	48A		

## **Description**

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

# **Applications**

- Power Management Functions
- Analog Switch

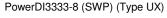
#### **Features**

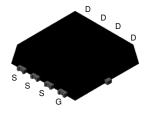
- Low RDS(ON) Ensures On-State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

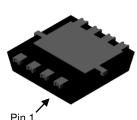
#### **Mechanical Data**

- Case: PowerDI<sup>®</sup>3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.03 grams (Approximate)

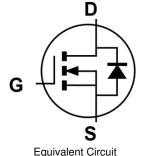




Top View



Bottom View



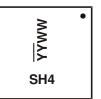
### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMT35M4LFVW-7	PowerDI3333-8 (SWP) (Type UX)	2,000/Tape & Reel
DMT35M4LFVW-13	PowerDI3333-8 (SWP) (Type UX)	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



 $\begin{array}{l} \underline{SH4} = Product\ Type\ Marking\ Code\\ \underline{\overline{YY}}WW = Date\ Code\ Marking\\ \overline{\overline{YY}} = Last\ Two\ Digits\ of\ Year\ (ex:\ 20=2020)\\ WW = Week\ Code\ (01\ to\ 53) \end{array}$ 



# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V <sub>DSS</sub>	30	V		
Gate-Source Voltage	$V_{GSS}$	±20	V		
Continuous Drain Current V 10V (Note C)	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	l <sub>D</sub>	16 13	А
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 6)	Steady State	$T_C = +25$ °C $T_C = +70$ °C	l <sub>D</sub>	60 48	А
Maximum Body Diode Forward Current (Note 6)	Is	2.3	Α		
Pulsed Drain Current (380µs Pulse, Duty Cycle = 19	I <sub>DM</sub>	110	Α		
Pulsed Drain Body Diode Forward Current (380µs F	I <sub>SM</sub>	110	Α		
Avalanche Current (L = 0.1mH) (Note 8)			las	22	Α
Avalanche Energy (L = 0.1mH) (Note 8)			Eas	25	mJ

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	PD	1.5	W	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	RθJA	83.3	°C/W
Total Power Dissipation (Note 6)		PD	2.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	RθJA	55	°C/W
Thermal Resistance, Junction to Case (Note 7)	R <sub>0</sub> JC	3.9	- C/VV	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

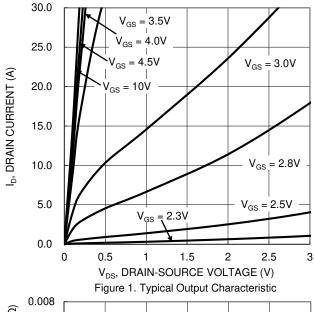
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)						•	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	lgss	_	_	±100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.15	_	2.5	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance	D		4.6	6	mΩ	V <sub>G</sub> S = 10V, I <sub>D</sub> = 20A	
Static Drain-Source On-Nesistance	R <sub>DS(ON)</sub>		6.5	9	11122	$V_{GS} = 4.5V, I_D = 15A$	
Diode Forward Voltage	V <sub>SD</sub>	_	0.7	1	V	V <sub>G</sub> S = 0V, I <sub>S</sub> = 1A	
DYNAMIC CHARACTERISTICS (Note 10)						•	
Input Capacitance	Ciss	_	982	_		V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	903	_	pF		
Reverse Transfer Capacitance	Crss	_	27	_		I = 1.0IVINZ	
Gate Resistance	Rg	_	2.2	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	7.9	_			
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	16.1	_	nC	V <sub>DD</sub> = 15V, I <sub>D</sub> = 9A	
Gate-Source Charge	Qgs	_	3.6	_	IIC		
Gate-Drain Charge	Qgd	_	1.2	_			
Turn-On Delay Time	tD(ON)	_	8.1	_			
Turn-On Rise Time	t <sub>R</sub>	_	2.2	_		$V_{DD} = 15V, V_{GS} = 10V,$ $R_g = 3\Omega, I_D = 9A$	
Turn-Off Delay Time	tD(OFF)	_	16.8	_	ns		
Turn-Off Fall Time	tr		5.7	_			

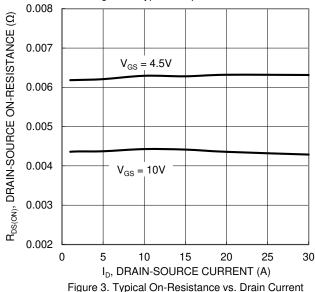
Notes:

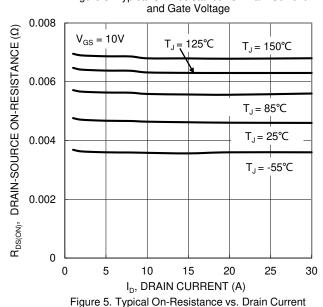
- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  9. Short duration pulse test used to minimize self-heating effect.
  10. Guaranteed by design. Not subject to product testing.



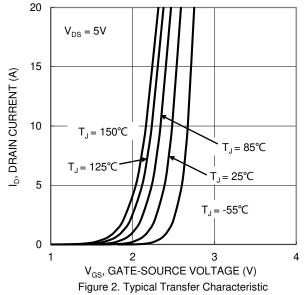








and Junction Temperature



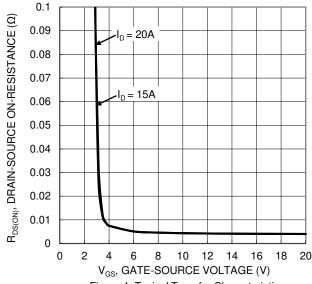


Figure 4. Typical Transfer Characteristic

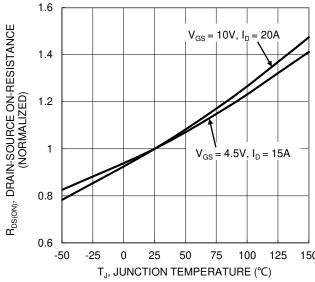


Figure 6. On-Resistance Variation with Junction Temperature





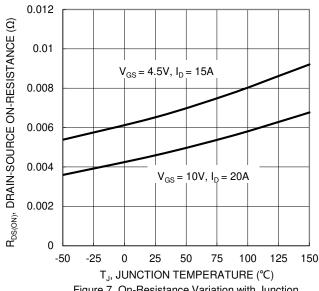
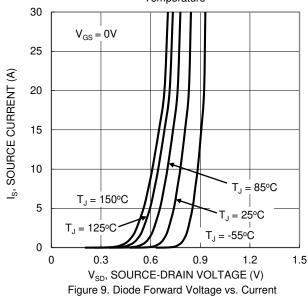


Figure 7. On-Resistance Variation with Junction Temperature



10 8 6 \$\frac{1}{2}\$ V<sub>DS</sub> = 15V, I<sub>D</sub> = 9A

 $\label{eq:Qg} \mathbf{Q_g} \; \text{(nC)}$  Figure 11. Gate Charge

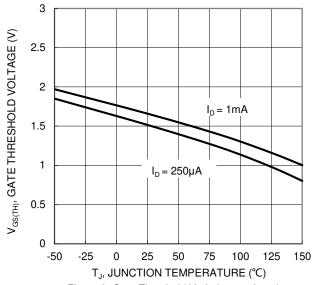
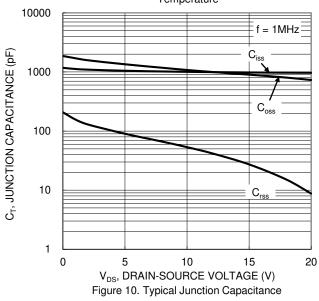


Figure 8. Gate Threshold Variation vs. Junction Temperature



1000 R<sub>DS(ON)</sub> Limited 100 ID, DRAIN CURRENT (A) 10  $P_{w} = 100 \mu s$ P<sub>W</sub> = 10ms 1  $P_W = 100ms$  $T_{J(Max)} = 150^{\circ}C$   $T_C = 25^{\circ}C$ Single Pulse DUT on Infinite Heatsink  $V_{GS} = 10V$ 0.01 0.1 10 100 V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V)

Figure 12. SOA, Safe Operation Area

0

0

2

14

16



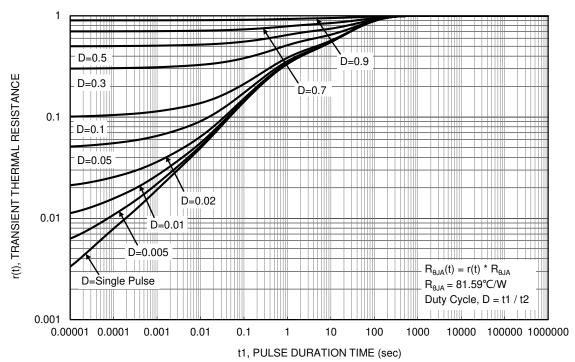


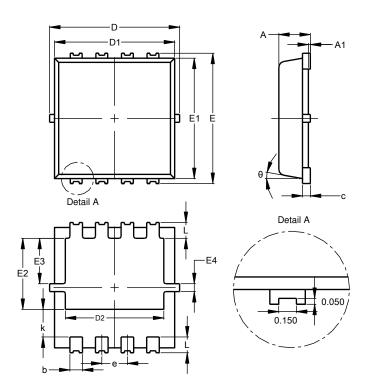
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI3333-8 (SWP) (Type UX)

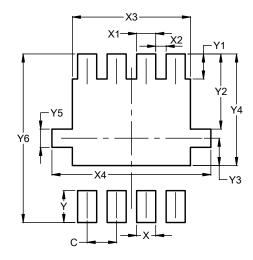


PowerDI3333-8 (SWP)						
(Type UX)						
Dim	Min	Тур				
Α	0.75	0.85	0.80			
<b>A</b> 1	0.00	0.05				
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	2.30	2.70	2.50			
Е	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е	_	_	0.65			
k	0.50	0.90	0.70			
L	0.30	0.50	0.40			
θ	0°	12°	10°			
All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)				
С	0.650				
Х	0.420				
X1	0.420				
X2	0.230				
Х3	2.600				
X4	3.500				
Υ	0.700				
Y1	0.550				
Y2	1.650				
Y3	0.600				
Y4	2.450				
Y5	0.400				
Y6	3.700				



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